

ABSTRACT OF THE DISCLOSURE

A semiconductor device is provided, which aims to reduce the standby power thereof by reducing the leak between a body and a drain with restraining the effect on a threshold voltage, in order to actualize the highly reliable semiconductor device. When extension regions are formed, an n-type impurity less diffusive than phosphorus (P^+), for example, arsenic (As^+) is used as an impurity. In addition to ordinary ion implantation with high dose (high concentration) and low acceleration energy, As^+ ions are implanted with low dose and high acceleration energy.